

# RJK03E7DPA

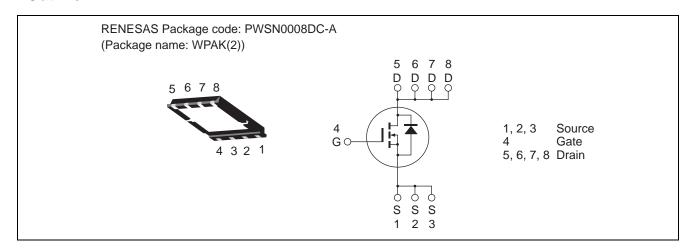
# Silicon N Channel Power MOS FET Power Switching

REJ03G1931-0210 Rev.2.10 May 20, 2010

#### **Features**

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  $R_{DS(on)} = 2.3 \ m\Omega \ typ. \ (at \ V_{GS} = 8 \ V)$
- Pb-free
- Halogen-free

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                                   | Symbol                      | Ratings     | Unit |
|--|-----------------------------|-------------|------|
| Drain to source voltage                | V <sub>DSS</sub>            | 30          | V    |
| Gate to source voltage                 | V <sub>GSS</sub>            | ±12         | V    |
| Drain current                          | I <sub>D</sub>              | 45          | A    |
| Drain peak current                     | I <sub>D(pulse)</sub> Note1 | 180         | A    |
| Body-drain diode reverse drain current | I <sub>DR</sub>             | 45          | A    |
| Avalanche current                      | I <sub>AP</sub> Note 2      | 22          | A    |
| Avalanche energy                       | E <sub>AR</sub> Note 2      | 48.4        | mJ   |
| Channel dissipation                    | Pch Note3                   | 45          | W    |
| Channel to case thermal impedance      | θch-c Note3                 | 2.78        | °C/W |
| Channel temperature                    | Tch                         | 150         | °C   |
| Storage temperature                    | Tstg                        | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. Tc = 25°C



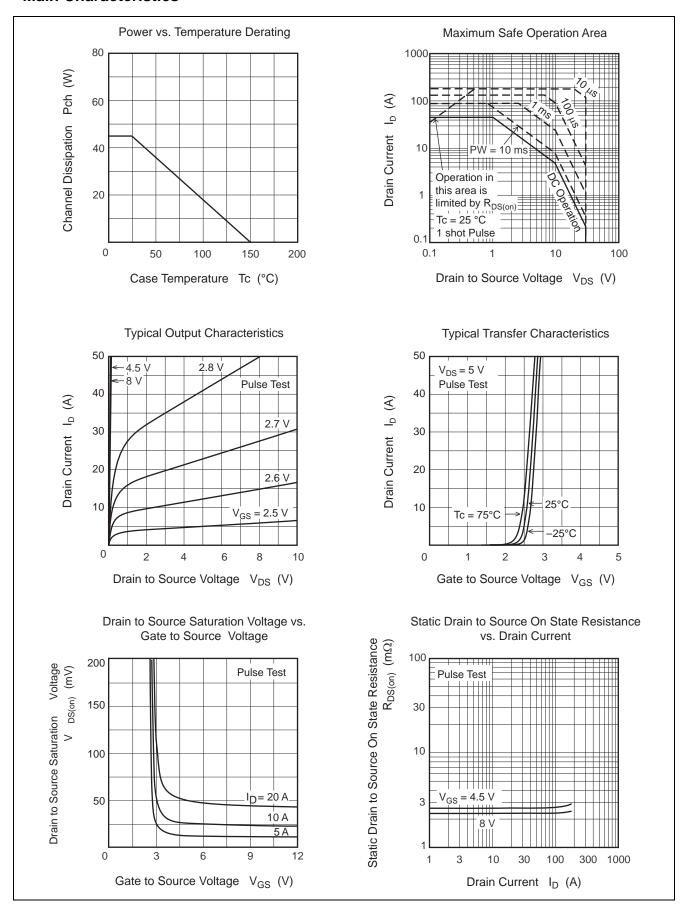
# **Electrical Characteristics**

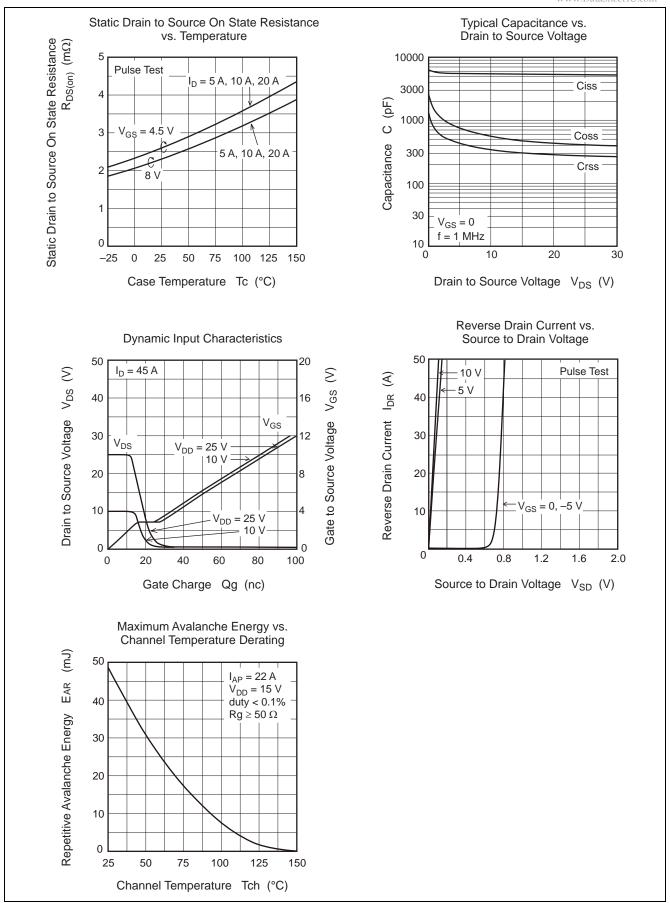
 $(Ta = 25^{\circ}C)$ 

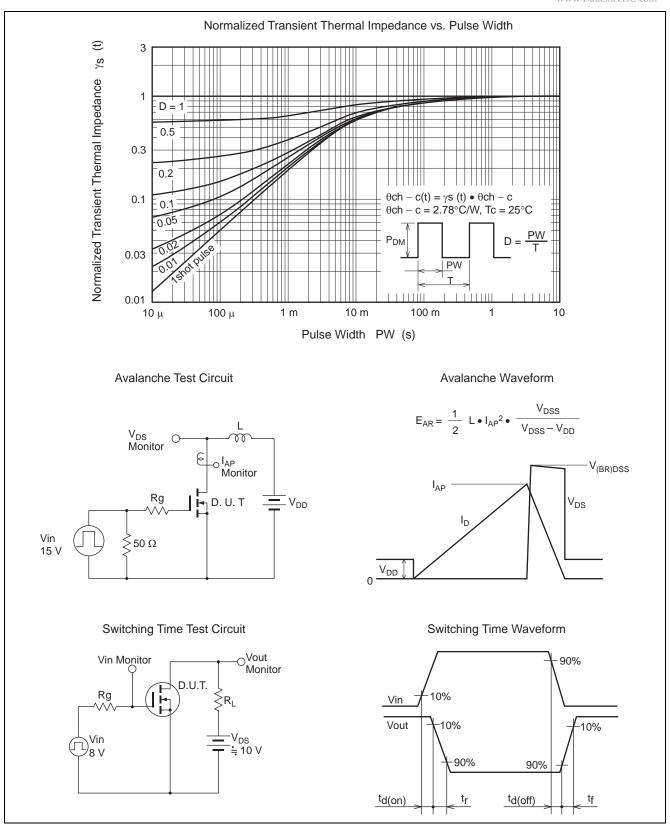
| Item                              | Symbol              | Min | Тур  | Max   | Unit | Test Conditions   |
|-----------------------------------|---------------------|-----|------|-------|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$       | 30  | _    | _     | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$                             |
| Gate to source leak current       | $I_{GSS}$           | _   | _    | ± 0.1 | μΑ   | $V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$                       |
| Zero gate voltage drain current   | I <sub>DSS</sub>    | 1   | _    | 1     | μΑ   | $V_{DS} = 30 \text{ V}, V_{GS} = 0$                           |
| Gate to source cutoff voltage     | $V_{GS(off)}$       | 1.2 | _    | 2.5   | ٧    | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$                   |
| Static drain to source on state   | R <sub>DS(on)</sub> | _   | 2.3  | 2.8   | mΩ   | $I_D = 22.5 \text{ A}, V_{GS} = 8.0 \text{ V}^{\text{Note4}}$ |
| resistance                        | R <sub>DS(on)</sub> | _   | 2.6  | 3.3   | mΩ   | $I_D = 22.5A, V_{GS} = 4.5 V^{Note4}$                         |
| Forward transfer admittance       | y <sub>fs</sub>     | _   | 120  | _     | S    | $I_D = 22.5 \text{ A}, V_{DS} = 5 \text{ V}^{\text{Note4}}$   |
| Input capacitance                 | Ciss                | _   | 5390 | 7450  | pF   | V <sub>DS</sub> = 10 V  |
| Output capacitance                | Coss                | _   | 560  | _     | pF   | $V_{GS} = 0$  |
| Reverse transfer capacitance      | Crss                |     | 340  | _     | pF   | f = 1 MHz   |
| Gate Resistance                   | Rg                  |     | 0.71 | 1.9   | Ω    |   |
| Total gate charge                 | Qg                  |     | 36   | _     | nC   | $V_{DD} = 10 \text{ V}$                                       |
| Gate to source charge             | Qgs                 |     | 16   | _     | nC   | $V_{GS} = 4.5 \text{ V}$                                      |
| Gate to drain charge              | Qgd                 |     | 11   | _     | nC   | I <sub>D</sub> = 45 A   |
| Turn-on delay time                | t <sub>d(on)</sub>  |     | 22   | _     | ns   | $V_{GS} = 8 \text{ V}, I_D = 22.5 \text{ A}$                  |
| Rise time                         | t <sub>r</sub>      |     | 7.7  | _     | ns   | $V_{DD} \cong 10 \text{ V}$                                   |
| Turn-off delay time               | t <sub>d(off)</sub> |     | 63   | _     | ns   | $R_L = 0.44 \Omega$   |
| Fall time                         | t <sub>f</sub>      |     | 12.5 | _     | ns   | $Rg = 4.7 \Omega$   |
| Body-drain diode forward voltage  | $V_{DF}$            |     | 0.80 | 1.04  | V    | $I_F = 45 \text{ A}, V_{GS} = 0^{\text{Note4}}$               |
| Body-drain diode reverse recovery | t <sub>rr</sub>     | _   | 26   | _     | ns   | $I_F = 45 \text{ A}, V_{GS} = 0$                              |
| time                              |                     |     |      |       |      | $di_F/dt = 100 A/ \mu s$                                      |

Notes: 4. Pulse test

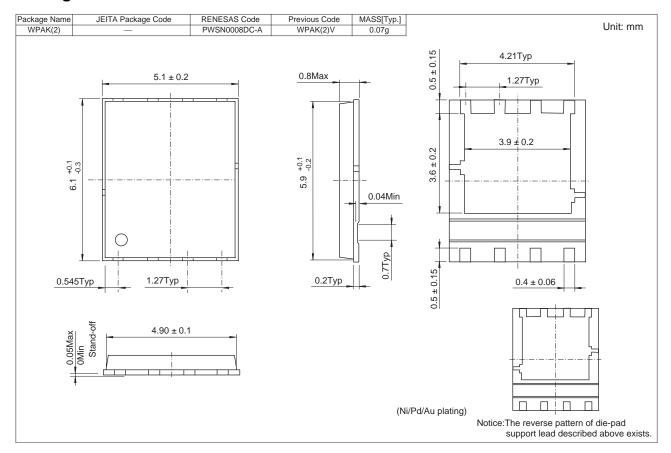
#### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

| Part No.          | Quantity | Shipping Container |
|-------------------|----------|--------------------|
| RJK03E7DPA-00-J53 | 3000 pcs | Taping             |

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